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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/728,135	12/03/2003	Vencent Chang	JCLA12578	6798

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EXAMINER
CHACKO DAVIS, DABORAH

ART UNIT	PAPER NUMBER
1756	

SHORTENED STATUTORY PERIOD OF RESPONSE	MAIL DATE	DELIVERY MODE
3 MONTHS	02/22/2007	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

Office Action Summary	Application No.	Applicant(s)	
	10/728,135	CHANG ET AL.	
	Examiner	Art Unit	
	Daborah Chacko-Davis	1756	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1)☒ Responsive to communication(s) filed on *20 November 2006*.

2a)☒ This action is **FINAL**. 2b)☐ This action is non-final.

3)☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4)☒ Claim(s) *1,3,4,6-8 and 10-15* is/are pending in the application.

4a) Of the above claim(s) _____ is/are withdrawn from consideration.

5)☐ Claim(s) _____ is/are allowed.

6)☒ Claim(s) *1,3,4,6-8 and 10-15* is/are rejected.

7)☐ Claim(s) _____ is/are objected to.

8)☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9)☐ The specification is objected to by the Examiner.

10)☐ The drawing(s) filed on _____ is/are: a)☐ accepted or b)☐ objected to by the Examiner.

Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11)☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12)☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

a)☐ All b)☐ Some * c)☐ None of:

1.☐ Certified copies of the priority documents have been received.

2.☐ Certified copies of the priority documents have been received in Application No. _____.

3.☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) ☐ Notice of References Cited (PTO-892)
2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
3) ☐ Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date _____.
4) ☐ Interview Summary (PTO-413) Paper No(s)/Mail Date. _____.
5) ☐ Notice of Informal Patent Application
6) ☐ Other: _____.

DETAILED ACTION

Claim Rejections - 35 USC § 112

1. The following is a quotation of the first paragraph of 35 U.S.C. 112:

> The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

2. Claims 1, and 11, are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. Claim 1, at lines 3-4, and claim 11, at lines 6-7, recite that "the protective layer is made of an acid-sensitive and radiation un-sensitive material".

Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

> (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

4. Claims 1,3-4, 6-8, 10-15, are rejected under 35 U.S.C. 103(a) as being unpatentable over U. S. Patent No. 6,939,664 (Huang et al., hereinafter referred to as Huang) in view of U. S. Patent No. 5,282,066 (Yu et al., hereinafter referred to as Yu).

Huang, in the abstract, in col 1, lines 65-67, in col 2, lines 1-4, in col 5, lines 11-19, in col 8, lines 56-67, in col 9, lines 35-50, in col 10, lines 22-67, in col 11, lines 1-60, discloses an immersion lithographic process comprising providing an imaging resist layer (the imaging resist layer is also an acid-generating resist layer and is considered the same as the acid supplying layer) that is coated onto a first layer of underlying planarizing layer or a multilayer (the underlying planarizing layer is disclosed as an acid generating resist layer in US 2002/0058204 cited in col 11, lines 50-54 of Huang), performing exposure on the multilayered substrate forming exposed and unexposed portions of the imaging resist, wherein the exposed resist layer undergoes acid-catalyzed reaction (acid generated from the resist layer upon exposure) resulting in the solubilization of the exposed portion of the photoresist layer, developing the exposed imaging layer so as to remove the exposed portions of the imaging layer and the corresponding underlayers, wherein the remaining non-soluble portions of the top imaging layer function as a mask structure for further processing. Huang, in col 11, lines 1-10, discloses that the exposed imaging layer is baked to promote acid-catalyzing reactions (solubilizing step) prior to the development i.e., the exposed portions of the imaging layer is altered in its polarity due to acid-catalyzed reactions (claims 1, 7, and 11-12,14-15). Huang, in col 4, lines 55-67, in col 5, lines 1-10, in col 8, lines 25-40, discloses that the acid is generated in the exposed portions of the photoresist (positive resist compositions) alters the polarity of the exposed portion of the photoresist (acid-catalyzed reactions in the exposed portions of the photoresist) and correspondingly alters the polarity of the imaging layer (protective layer), resulting in soluble (hydrophilic)

and insoluble (hydrophobic) portions in the imaging and underlying layers, wherein the soluble portions are removed in the developing step (claims 3-4, 8). Huang in col 14, lines 49-53, discloses forming the photoresist layer on an ARC (anti-reflection layer) coated wafer (claims 6, 10, and 13).

The difference between the claims and Huang is that Huang does not disclose forming a protective layer on the resist layer and/or the acid supplying layer. Huang does not disclose that the acid produced in the imaging resist layer is diffused in the protective layer.

Yu, in col 6, lines 15-20, discloses that a protective layer is formed on the photoresist layer.

Therefore, it would be obvious to a skilled artisan to modify Huang by employing a protective layer on the imaging resist layer because Yu, in col 6, lines 12-26, discloses that the protective layer on the photosensitive layer (imaging resist layer) prevents the immersion oils or liquids from contacting or interacting with the imaging resist layer, and it would be obvious to a skilled artisan to solubilize the protective layer suggested by Yu after exposure because Huang, in col 9, lines 52-67, and in col 10, lines 1-6, discloses that the imaging resist layer is an acid generating layer, which upon exposure releases acid in the exposed regions and is subjected to post-exposure heating, as a result of which the thermal energy supplied makes the released acid mobile and interactive to its vicinities and promotes acid-catalyzed reactions i.e., will solubilize any layer (underlying or topcoat protective) in the exposed portions.

Response to Arguments

5. Applicant's arguments filed 11/20/2006 have been fully considered but they are not persuasive. The 103 rejection made in the previous office action has been maintained.

A) Applicants argue that Huang does not disclose forming a protective layer on the resist layer.

Huang is not depended upon to disclose the formation of a protective layer on the acid supplying layer. Yu teaches forming a protective layer on a photoresist or an acid-supplying layer.

B) Applicants argue that Huang does not disclose an acid supplying layer.

Huang in col 10, lines 54-67, in col 11, lines 1-15, teaches forming a photoresist layer on a planarizing underlayer, wherein the photoresist layer has an acid generator and is considered the same as the acid supplying layer. Huang in col 11, lines 21-55, teaches a planarizing underlayer under the photoresist layer (considered here as the acid supplying layer) wherein the planarizing underlayer layer is a photosensitive polymer and is considered here as the photoresist layer and (also taught in detail in US2002 /0058204 incorporated in Huang in col 11, lines 52-54) is a radiation sensitive and acid generating resist layer. Therefore, Huang does teach an acid supplying layer.

C) Applicants argue that neither Huang nor Yu teaches that the protective layer is an acid sensitive and radiation insensitive material.

Huang is not depended upon to teach a protective layer. Yu teaches a protective layer formed over a photoresist/acid generating layer. Yu, in col 6, lines 12-20, and in

col 8,lines 19-32, discloses that the protective cover that covers the recording layer (photoresist or imaging resist layer) is inherently non-sensitive to radiation (not curing or crosslinking occurs on the protective covering or barrier even upon exposure to laser and intense UV radiation), and that the protective barrier only prevents the diffusion of the immersion fluids into the photoresist or imaging recording layer, and the protective layer is removed after developing. Huang teaches that the acid generated in the acid generating layer is mobile and permeates its immediate vicinities, and therefore would permeate the protective barrier of Yu (i.e., the protective barrier of Yu is acid sensitive).

Conclusion

6. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Daborah Chacko-Davis whose telephone number is (571) 272-1380. The examiner can normally be reached on M-F 9:30 - 6:00. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Mark F Huff can be reached on (571) 272-1385. The fax phone number for the organization where this application or proceeding is assigned is (571) 273-8300. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

dcd

February 12, 2007.

MARK F. HUFF
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 1700